


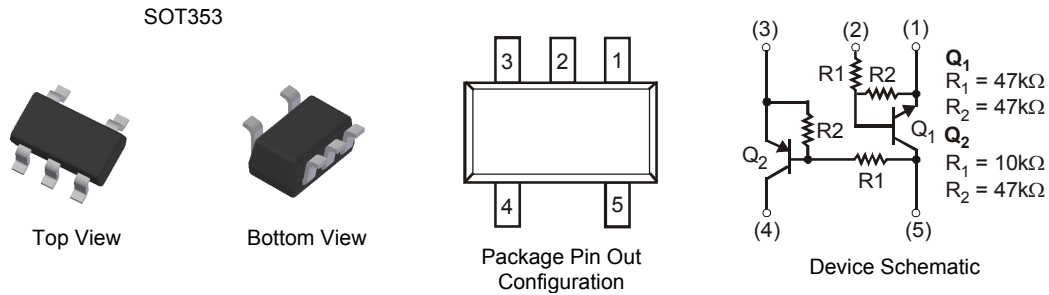
**DUAL COMPLEMENTARY PRE-BIASED TRANSISTORS**

**Features**

- Ultra-Small Surface Mount Package
- Epitaxial Planar Die Construction
- Surface Mount Package Suited for Automated Assembly
- Simplifies Circuit Design and Reduces Board Space
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP capable (Note 4)**

**Mechanical Data**

- Case: SOT353
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per MIL-STD-202, Method 208 
- Weight: 0.006 grams (approximate)

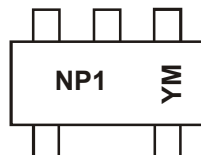


**Ordering Information** (Notes 4 & 5)

| Part Number | Compliance | Marking | Reel size (inch) | Tape width (mm) | Quantity per reel |
|-------------|------------|---------|------------------|-----------------|-------------------|
| UMC4N-7     | AEC-Q101   | NP1     | 7                | 8               | 3,000             |
| UMC4NQ-7    | Automotive | NP1     | 7                | 8               | 3,000             |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
  5. For packaging details, go to our website at <http://www.diodes.com>.

**Marking Information**



NP1 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: A = 2013)  
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2010 | 2011 | 2012 | 2013 | 2014 | 2015 | 2016 | 2017 |
|------|------|------|------|------|------|------|------|------|
| Code | X    | Y    | Z    | A    | B    | C    | D    | E    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

**Maximum Ratings, Pre-Biased NPN Transistor, Q<sub>1</sub>** (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic    | Symbol          | Value      | Unit |
|-------------------|-----------------|------------|------|
| Supply Voltage    | V <sub>CC</sub> | 50         | V    |
| Input Voltage     | V <sub>IN</sub> | -10 to +40 | V    |
| Output Current    | I <sub>O</sub>  | 30         | mA   |
| Collector Current | I <sub>C</sub>  | 100        | mA   |

**Maximum Ratings, Pre-Biased PNP Transistor, Q<sub>2</sub>** (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic    | Symbol          | Value     | Unit |
|-------------------|-----------------|-----------|------|
| Supply Voltage    | V <sub>CC</sub> | -50       | V    |
| Input Voltage     | V <sub>IN</sub> | -40 to +6 | V    |
| Output Current    | I <sub>O</sub>  | -100      | mA   |
| Collector Current | I <sub>C</sub>  | -100      | mA   |

**Thermal Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic                                       | Symbol                            | Value       | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 6)                           | P <sub>D</sub>                    | 150         | mW   |
| Thermal Resistance, Junction to Ambient Air (Note 6) | R <sub>θJA</sub>                  | 833         | °C/W |
| Operating and Storage Temperature Range              | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

Notes: 6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

**Electrical Characteristics, Pre-Biased NPN Transistor, Q<sub>1</sub>** (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic                  | Symbol                         | Min  | Typ | Max  | Unit | Test Condition   |
|---------------------------------|--------------------------------|------|-----|------|------|--|
| Input Voltage                   | (Note 7) V <sub>I(OFF)</sub>   | 0.5  | —   | —    | V    | V <sub>CC</sub> = 5V, I <sub>O</sub> = 100μA             |
|                                 | (Note 8) V <sub>I(ON)</sub>    | —    | —   | 3    | V    | V <sub>O</sub> = 0.3V, I <sub>O</sub> = 2mA              |
| Output Voltage                  | V <sub>O(ON)</sub>             | —    | 0.1 | 0.3  | V    | I <sub>O</sub> / I <sub>I</sub> = 10mA/0.5 mA            |
| Input Current                   | I <sub>I</sub>                 | —    | —   | 0.18 | mA   | V <sub>I</sub> = 5V                                      |
| Output Current                  | I <sub>O(OFF)</sub>            | —    | —   | 0.5  | μA   | V <sub>CC</sub> = 50V, V <sub>I</sub> = 0V               |
| DC Current Gain                 | G <sub>I</sub>                 | 68   | —   | —    | —    | V <sub>O</sub> = 5V, I <sub>O</sub> = 5mA                |
| Gain-Bandwidth Product (Note 9) | f <sub>T</sub>                 | —    | 250 | —    | MHz  | V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA, f = 100MHz |
| Input Resistance                | R <sub>1</sub>                 | 32.9 | 47  | 61.1 | kΩ   | —  |
| Resistance Ratio                | R <sub>2</sub> /R <sub>1</sub> | 0.8  | 1   | 1.2  | —    | —  |

Note: 7. The device is guaranteed to be in "OFF" state with V<sub>I(OFF)</sub> up to 0.5V  
 8. The device is guaranteed to be in "ON" state with V<sub>I(ON)</sub> starting from 3V  
 9. Characteristic of Transistor – for reference only.

**Electrical Characteristics, Pre-Biased PNP Transistor, Q<sub>2</sub>** (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic                   | Symbol                         | Min  | Typ  | Max   | Unit | Test Condition   |
|----------------------------------|--------------------------------|------|------|-------|------|--|
| Input Voltage                    | (Note 10) V <sub>I(OFF)</sub>  | -0.3 | —    | —     | V    | V <sub>CC</sub> = -5V, I <sub>O</sub> = -100μA           |
|                                  | (Note 11) V <sub>I(ON)</sub>   | —    | —    | -1.4  | V    | V <sub>O</sub> = -0.3V, I <sub>O</sub> = -1mA            |
| Output Voltage                   | V <sub>O(ON)</sub>             | —    | -0.1 | -0.3  | V    | I <sub>O</sub> / I <sub>I</sub> = -5mA/-0.25 mA          |
| Input Current                    | I <sub>I</sub>                 | —    | —    | -0.88 | mA   | V <sub>I</sub> = -5V                                     |
| Output Current                   | I <sub>O(OFF)</sub>            | —    | —    | -0.5  | μA   | V <sub>CC</sub> = -50V, V <sub>I</sub> = 0V              |
| DC Current Gain                  | G <sub>I</sub>                 | 68   | —    | —     | —    | V <sub>O</sub> = -5V, I <sub>O</sub> = -5mA              |
| Gain-Bandwidth Product (Note 12) | f <sub>T</sub>                 | —    | 250  | —     | MHz  | V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz |
| Input Resistance                 | R <sub>1</sub>                 | 7    | 10   | 13    | kΩ   | —  |
| Resistance Ratio                 | R <sub>2</sub> /R <sub>1</sub> | 3.7  | 4.7  | 5.7   | —    | —  |

Note: 10. The device is guaranteed to be in "OFF" state with V<sub>I(OFF)</sub> up to -0.3V  
 11. The device is guaranteed to be in "ON" state with V<sub>I(ON)</sub> starting from -1.4V  
 12. Characteristic of Transistor – for reference only.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$  unless otherwise specified.)

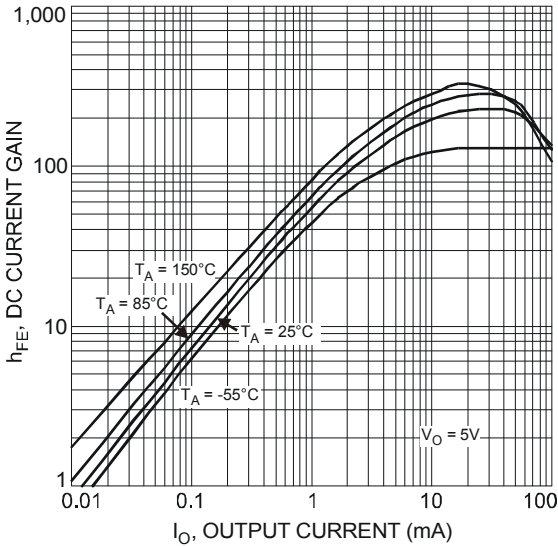


Fig. 1 Typical DC Current Gain vs. Output Current (Q1, NPN)

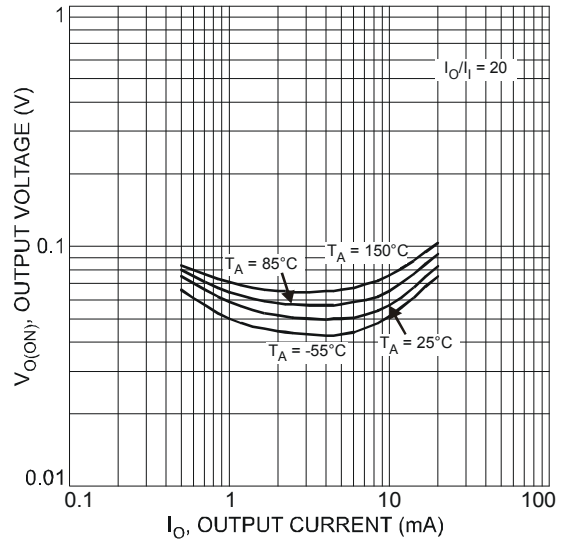


Fig. 2 Typical Output Voltage vs. Output Current (Q1, NPN)

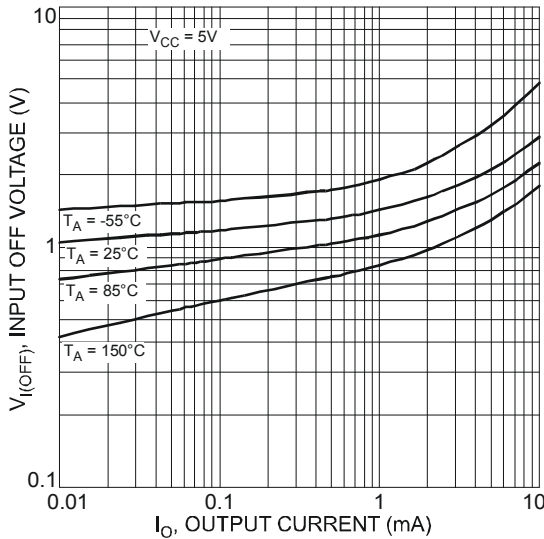


Fig. 3 Typical Input OFF Voltage vs. Output Current (Q1, NPN)

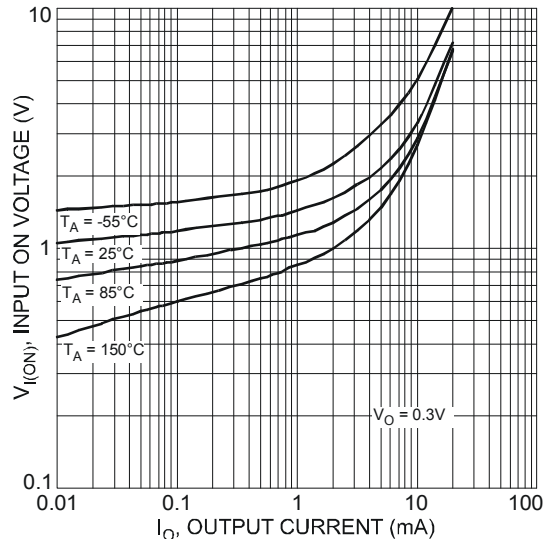
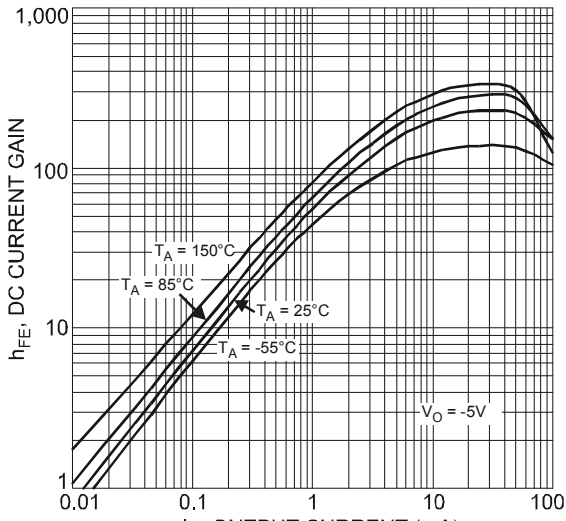
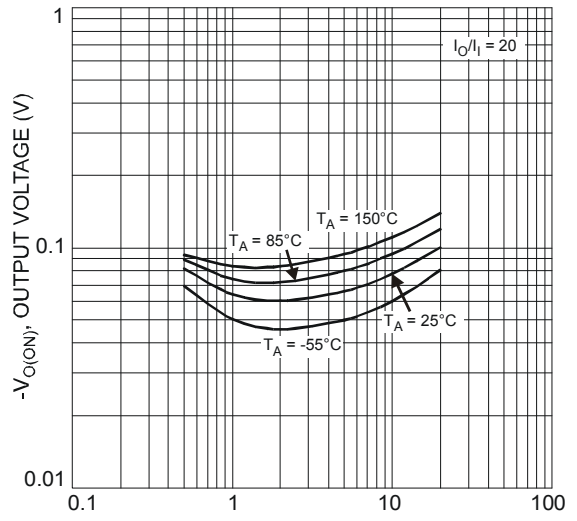


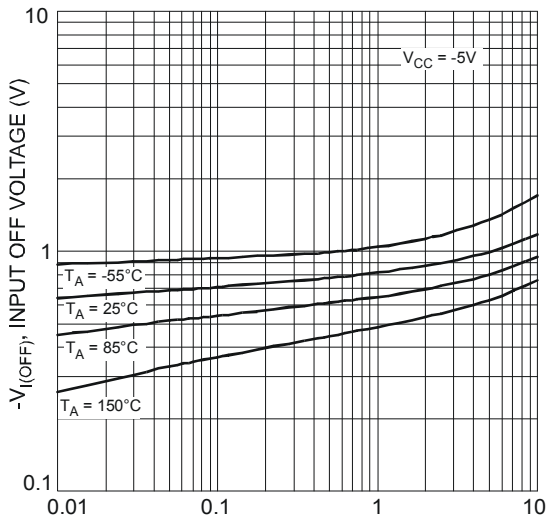
Fig. 4 Typical Input ON Voltage vs. Output Current (Q1, NPN)



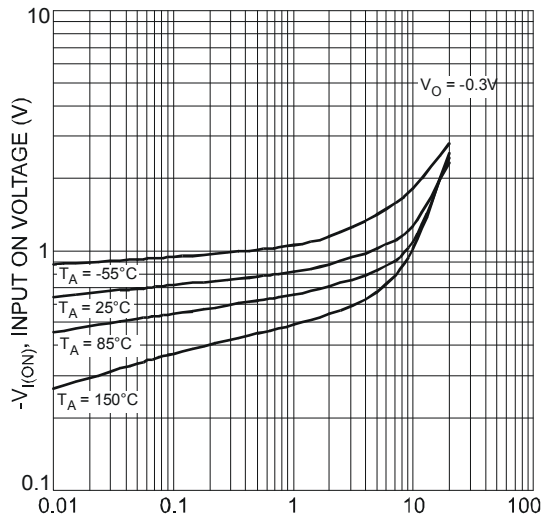
$-I_O$ , OUTPUT CURRENT (mA)  
Fig. 5 Typical DC Current Gain vs. Output Current (Q2, PNP)



$-I_O$ , OUTPUT CURRENT (mA)  
Fig. 6 Typical Output Voltage vs. Output Current (Q2, PNP)



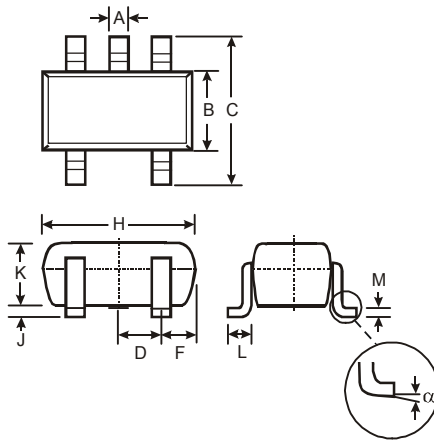
$-I_O$ , OUTPUT CURRENT (mA)  
Fig. 7 Typical Input Off Voltage vs. Output Current (Q2, PNP)



$-I_O$ , OUTPUT CURRENT (mA)  
Fig. 8 Typical Input On Voltage vs. Output Current (Q2, PNP)

**Package Outline Dimensions**

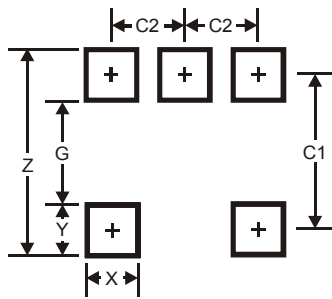
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



| SOT353                      |          |      |
|-----------------------------|----------|------|
| Dim                         | Min      | Max  |
| A                           | 0.10     | 0.30 |
| B                           | 1.15     | 1.35 |
| C                           | 2.00     | 2.20 |
| D                           | 0.65 Typ |      |
| F                           | 0.40     | 0.45 |
| H                           | 1.80     | 2.20 |
| J                           | 0        | 0.10 |
| K                           | 0.90     | 1.00 |
| L                           | 0.25     | 0.40 |
| M                           | 0.10     | 0.22 |
| α                           | 0°       | 8°   |
| <b>All Dimensions in mm</b> |          |      |

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.5           |
| G          | 1.3           |
| X          | 0.42          |
| Y          | 0.6           |
| C1         | 1.9           |
| C2         | 0.65          |

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